

**OBJECTIVE
SPECIFICATIONS**

Features

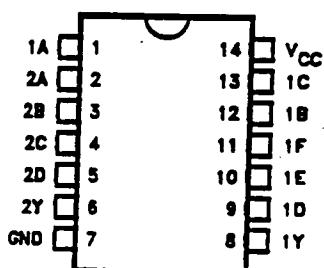
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5V$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
74AHCT: -40°C to +85°C
54AHCT: -55°C to +125°C

Function Table

Inputs						Output IY	
IA	IB	IC	ID	IE	IF	'51	'58
H	H	H	X	X	X	L	H
X	X	X	H	H	H	L	H
Any Other Combination						H	L

Inputs				Output 2Y	
2A	2B	2C	2D	'51	'58
H	H	X	X	L	H
X	X	H	H	L	H
Any Other Combination				H	L

Pin Configuration



0014-1

Dual AND-OR-Invert Gates and Dual AND-OR Gates

Description

The '51 performs the following Boolean functions:

$$\begin{aligned} IY &= \overline{(IA \bullet IB \bullet IC)} + (ID \bullet IE \bullet IF) \\ 2Y &= \overline{(2A \bullet 2B)} + (2C \bullet 2D) \end{aligned}$$

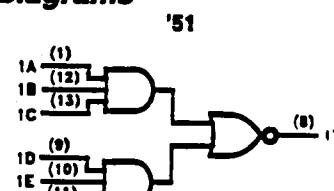
The '58 performs:

$$\begin{aligned} IY &= (IA \bullet IB \bullet IC) + (ID \bullet IE \bullet IF) \\ 2Y &= (2A \bullet 2B) + (2C \bullet 2D) \end{aligned}$$

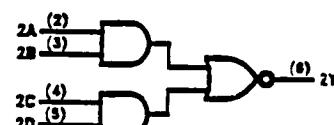
Fabrication using ISI proprietary ICE-MOS process, these devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

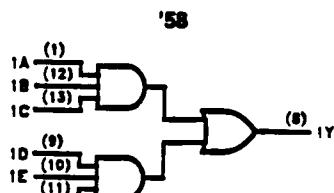
Logic Diagrams



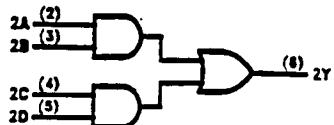
'51



0014-2



'58



0014-3

Absolute Maximum Ratings*

Supply Voltage Range, V_{cc}	-0.5V to 7V
DC Input Diode Current, I_{ik} ($V_i < -0.5V$ or $V_i > V_{cc} + 0.5V$).....	± 20 mA
DC Output Diode Current, I_{ok} ($V_o < -0.5V$ or $V_o > V_{cc} + 0.5V$).....	± 20 mA
Continuous Output Current Per Pin, I_o ($-0.5V < V_o < V_{cc} + 0.5V$).....	± 35 mA
Continuous Current Through V_{cc} or GND pins.....	± 125 mA
Storage Temperature Range, T_{STG}	-65°C to +150°C
Power Dissipation Per Package, P_D •	500 mW

*Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

•Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C
Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{cc} 4.5V to 5.5V
DC Input & Output Voltages*, V_{IN} , V_{OUT} 0V to V_{cc}

Operating Temperature

Range	74AHCT: -40°C to +85°C
	54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r , t_f Max 500 ns

*Unused inputs must always be tied to an appropriate logic voltage level (either V_{cc} or GND)

DC Electrical Characteristics ($V_{cc} = 5V \pm 10\%$ Unless Otherwise Specified)

Sym	Parameter	Test Conditions	$T_A = 25^\circ C$		$74AHCT$	$54AHCT$	Unit
			Typ		$T_A = -40^\circ C$ to $+85^\circ C$	$T_A = -55^\circ C$ to $+125^\circ C$	
V_{IH}	Minimum High-Level Input Voltage			2.0	2.0	2.0	V
V_{IL}	Maximum Low-Level Input Voltage			0.8	0.8	0.8	V
V_{OH}	Minimum High-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_o = -20 \mu A$ $I_o = -4 mA$	V_{cc} 4.2	$V_{cc} -0.1$ 3.98	$V_{cc} -0.1$ 3.84	$V_{cc} -0.1$ 3.7	V
V_{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_o = 20 \mu A$ $I_o = 4 mA$ $I_o = 8 mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{cc}$ or GND		± 0.1	± 1.0	± 1.0	μA
I_{cc}	Maximum Quiescent Supply Current	$V_{IN} = V_{cc}$ or GND $I_{OUT} = 0 \mu A$		2.0	20.0	40.0	μA

AC Electrical Characteristics (Input $t_r, t_f \leq 2$ ns), AHCT51, AHCT58

Sym	Parameter	Conditions •	$T_A = 25^\circ C$	$T_A = -40^\circ C$ to $+85^\circ C$	$T_A = -55^\circ C$ to $+125^\circ C$	Unit
			VCC - 5.0V	V _{CC} = 5.0V $\pm 10\%$	V _{CC} = 5.0V $\pm 10\%$	
t_{PLH}	<i>Maximum Propagation Delay</i>	$C_L = 50$ pF	9	15	18	ns
			9	15	18	
C_{IN}	<i>Maximum Input Capacitance</i>		5			pF
C_{PD}	<i>Power Dissipation Capacitance*</i>	(per gate)	15			pF

* C_{PD} determines the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$

•For AC switching test circuits and timing waveforms see section 2.